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0.3W, PNP Plastic-Encapsulate Transistor

FEATURES

- Low power loss, high efficiency
- Ideal for automated placement
- High surge current capability
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Lighting application
- On-board DC/DC converter

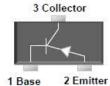
MECHANICAL DATA

- Case: SOT-23
- Molding compound meets UL 94 V-0 flammability rating
- Moisture sensitivity level: level 1, per J-STD-020
- Packing code with suffix "G" means green compound (halogen-free)
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1A whisker test
- Weight: 0.008grams (approximately)

KEY PARAMETERS					
PARAMETER	VALUE	UNIT			
V_{CBO}	-50	V			
$V_{\sf CEO}$	-45	V			
V_{EBO}	-5	V			
I _C	-0.5	Α			
h _{FE}	250-600				
Package	SOT-23				
Configuration	Single Dice				







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER	SYMBOL	BC807- 16	BC807- 25	BC807- 40	UNIT	
Marking code on the device			5A	5B	5C	
Power dissipation		P_{D}	0.3		W	
Collector-base voltage, emitter open $I_C = -10 \mu A$, $I_E = 0$		V _{CBO}	-50		V	
Collector-emitter voltage, base open $I_C = -10 \text{ mA}, I_B = 0$		V_{CEO}	-45		V	
Emitter-base voltage, collector open $I_E = -1 \mu A, I_C = 0$		V_{EBO}	-5		V	
Collector current, dc	I _C	-0.5		Α		
Junction temperature		T _J	-55 to +150		°C	
Storage temperature	T _{STG}	_	55 to +15	0	°C	

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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)							
PARAMETER	CONDITIONS		SYMBOL	MIN	TYP	MAX	UNIT
Collector cutoff current, emitter	$V_{CB} = -45 \text{ V}, I_{E}$	= 0		-	-	-0.1	
open	$V_{CB} = -40 \text{ V}, I_{B}$	= 0	I _{CBO}	-	-	-0.2	μΑ
Emitter cutoff current, collector open	V _{EB} = -4 V, I _C = 0		I _{EBO}	-	-	-0.1	μΑ
DC current gain	$V_{CE} = -1 V$, $I_{C} = -100 \text{ mA}$	BC807-16	h _{FE}	100	-	250	
		BC807-25		160	-	400	
		BC807-40		250	-	600	
Collector-emitter saturation voltage	I _C = -500 mA, I _B = -50 mA		V _{CE(sat)}	-	-	-0.7	V
Base-emitter saturation voltage	I _C = -500 mA, I _B = -50 mA		$V_{BE(sat)}$	-	-	-1.2	V
Transition frequency	$V_{CE} = -5 \text{ V}$, $I_{C} = -10 \text{ mA}$, $f = 50 \text{MHz}$		f _T	100	-	-	MHz

ORDERING INFORMATION				
PART NO.	PACKING CODE	PACKING CODE SUFFIX(*)	PACKAGE	PACKING
BC807-XX (Note 1)	RF	G	SOT-23	3K / 7" Reel

Notes:

^{*:} optional available

EXAMPLE				
EXAMPLE P/N	PART NO.	PACKING CODE	PACKING CODE SUFFIX	DESCRIPTION
BC807-16 RFG	BC807-16	RF	G	Green compound

^{1. &}quot;xx" is Device Code is"16" and "25" and "40"



CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.1 Power Derating Curve

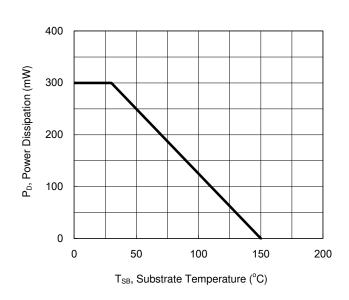


Fig. 2 Gain Bandwidth Product VS.

Collector Current

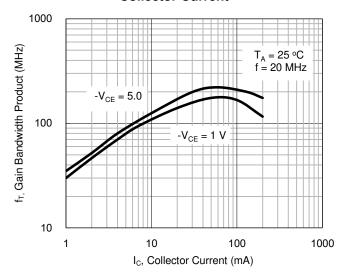


Fig.3 Collector Sat Voltage VS. Collector Current

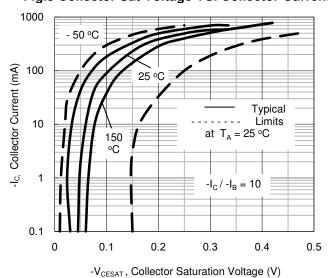
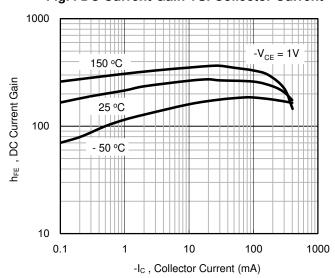


Fig.4 DC Current Gain VS. Collector Current





CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.5 Typical Emitter-Collector Characteristics

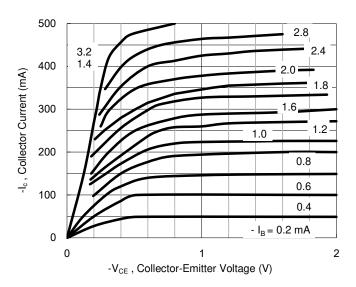
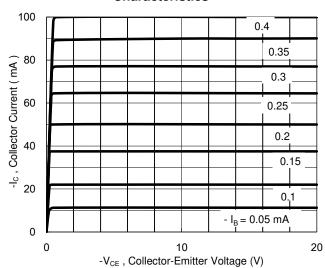
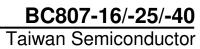


Fig. 6 Typical Transient Thermal Characteristics



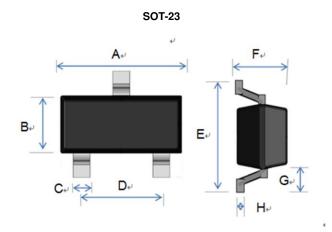
Version:H1702

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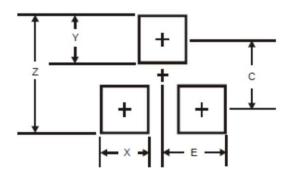


PACKAGE OUTLINE DIMENSION



DIM.	Unit(mm)		Unit(inch)		
DIW.	Min	Max	Min	Мах	
Α	2.70	3.10	0.106	0.122	
В	1.10	1.50	0.043	0.059	
С	0.30	0.51	0.012	0.020	
D	1.78	2.04	0.070	0.080	
E	2.10	2.64	0.083	0.104	
F	0.89	1.30	0.035	0.051	
G	0.55 REF		0.022	REF	
Н	0.10 REF		0.004	REF	

SUGGEST PAD LAYOUT



DIM.	Unit(mm)	Unit(inch)		
	TYP	TYP		
Z	2.8	0.11		
Х	0.7	0.03		
Υ	0.9	0.04		
С	1.9	0.07		
Е	1.0	0.04		



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